



# 《风光欣》技术资料

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## SS8050

NPN EPITAXIAL SILICON TRANSISTOR

2W OUTPUT AMPLIFIER OF PORTABLE

RADIOS IN CLASS

B PUSH-PULL OPERATION

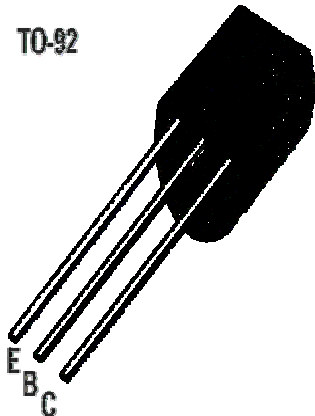
\* Complimentary to **SS8550**

\* Collector Current  $I_{cm} = 1.5A$

\* Collector Dissipation:  $P_c = 2W$  ( $T_c = 25$  )

### ABSOLUTE MAXIMUM RATINGS( $T_A = 25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	40	V
Collector-Emitter Voltage	$V_{CEO}$	25	V
Emitter -Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_c$	1.5	A
Collector Dissipation	$P_c$	1	W
Junction Temperature	$T_j$	150	
Storage Temperature	$T_{STG}$	-65 ~150	



### ELECTRICAL CHARACTERISTICS ( $T_A = 25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_c = 100 \mu A$ $I_E = 0$	40			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_c = 2mA$ $I_B = 0$	25			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E = 100 \mu A$ $I_c = 0$	6			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 35V$ $I_E = 0$			100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 6V$ $I_c = 0$			100	nA
DC Current Gain	HFE1	$V_{CE} = 1V$ $I_c = 5mA$	45	135		
	HFE2	$V_{CE} = 1V$ $I_c = 100mA$	85	160	300	
	HFE3	$V_{CE} = 1V$ $I_c = 800mA$	40	110		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 800mA$ $I_B = 80mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = 800mA$ $I_B = 80mA$		0.98	1.2	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE} = 1V$ $I_c = 10mA$		0.66	1.0	V
Output Capacitance (f=1MHz)	$C_{OB}$	$V_{CB} = 10V$ $I_E = 0$		9		pF
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 10V$ $I_c = 50mA$	100	190		MHz

### HFE 2 : CLASSIFICATION

Classification	B	C	D
HFE	85-160	120-200	160-300